SBM1040

10A LOW VF SCHOTTKY BARRIER RECTIFIER
POWERMITE®3

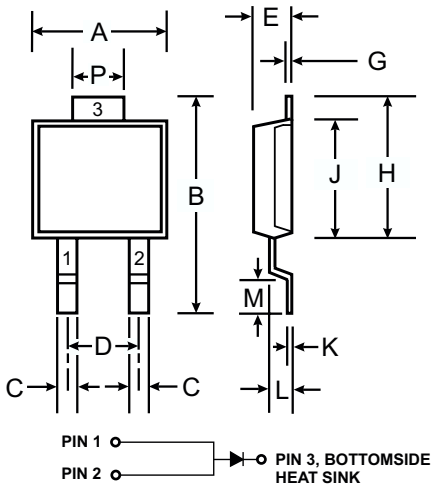
NEW PRODUCT

Features

- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Max Junction Temperature Rating
- Very Low Forward Voltage Drop
- Very Low Leakage Current
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- Plastic Material: UL Flammability Classification Rating 94V-0

Mechanical Data

- Case: POWERMITE®3, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: See Diagram
- Weight: 0.072 grams (approx.)
- Marking information: See sheet 3



Note: Pins 1 & 2 must be electrically connected at the printed circuit board.

POWERMITE®3		
Dim	**Min**	**Max**
A	4.03	4.09
B	6.40	6.61
C	.889 NOM	
D	1.83 NOM	
E	1.10	1.14
G	.178 NOM	
H	5.01	5.17
J	4.37	4.43
K	.178 NOM	
L	.71	.77
M	.36	.46
P	1.73	1.83
All Dimensions in mm		

Maximum Ratings @ T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Average Rectified Output Current (see also Figure 4)	I_O	10	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave Superimposed on Rated Load (JEDEC Method) @TC = 88°C	I_{FSM}	150	A
Typical Thermal Resistance Junction to Soldering Point	$R_{\theta JS}$	2.5	°C/W
Operating Temperature Range	T_j	-65 to +150	°C
Storage Temperature Range	T_{STG}	-65 to +150	°C

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	40	—	—	V	I_R = 1mA
Forward Voltage (Note 1)	V_{FM}	— — —	0.45 — 0.47	0.49 0.41 0.51	V	I_F = 8A, T_S = 25°C I_F = 8A, T_S = 125°C I_F = 10A, T_S = 25°C
Peak Reverse Current (Note 1)	I_{RM}	— —	0.1 12.5	0.3 25	mA	T_S = 25°C, V_R = 35V T_S = 100°C, V_R = 35V
Junction Capacitance	C_j	—	700	—	pF	f = 1.0MHz, V_R = 4.0V DC

Notes: 1. Short duration test pulse used to minimize self-heating effect.

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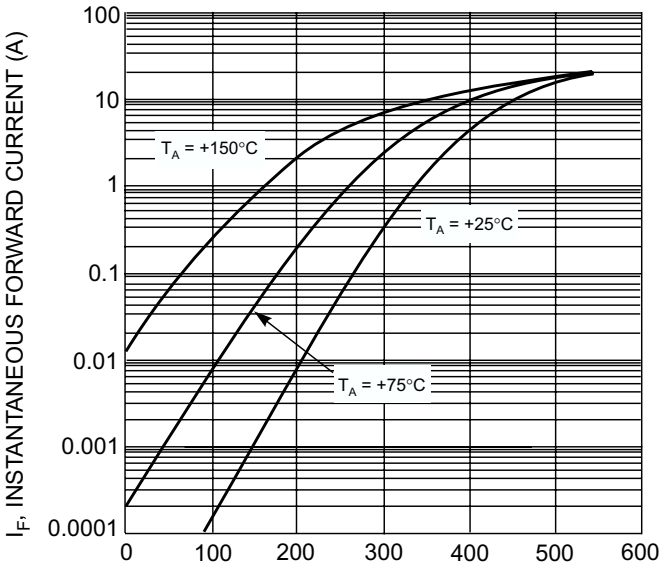

Fig. 1 Typical Forward Characteristics

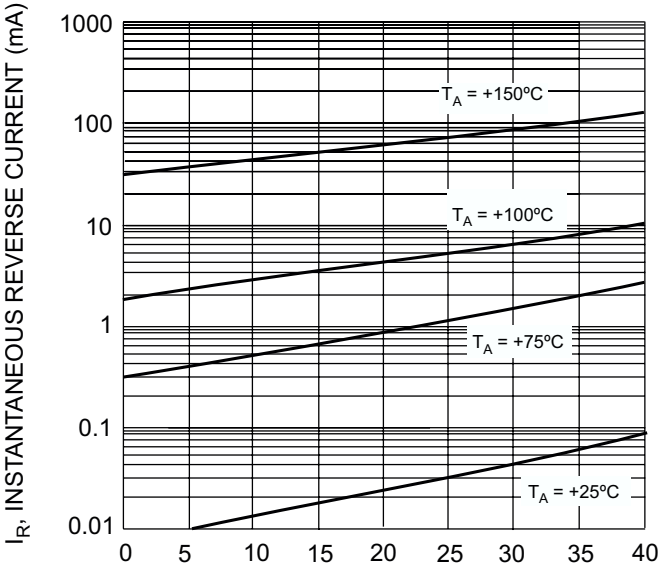

Fig. 2 Typical Reverse Characteristics

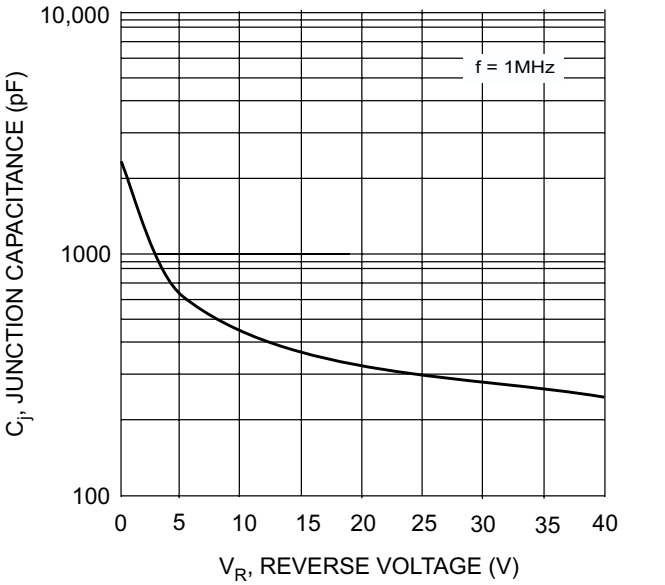

Fig. 3 Typical Junction Capacitance vs. Reverse Voltage

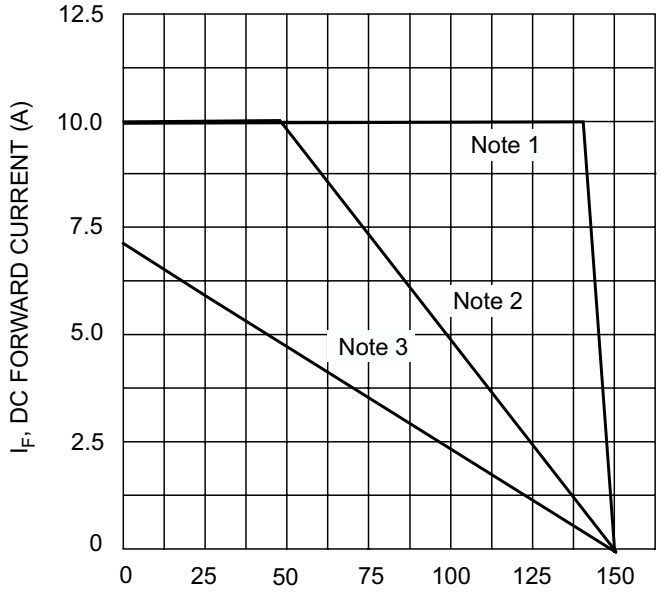

Fig. 4 DC Forward Current Derating

Notes:
1. $T_A = T_{SOLDERING\ POINT}$, $R_{\theta JS}$ = 2.5°C/W, $R_{\theta SA}$ = 0°C/W.
2. Device mounted on GETEK substrate, 2"x2", 2 oz. copper, double-sided, cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0". $R_{\theta JA}$ in range of 15-30°C/W.
3. Device mounted on FR-4 substrate, 2"x2", 2 oz. copper, single-sided, pad layout as per Diodes Inc. suggested pad layout document AP02001 which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf. $R_{\theta JA}$ in range of 60-75°C/W.

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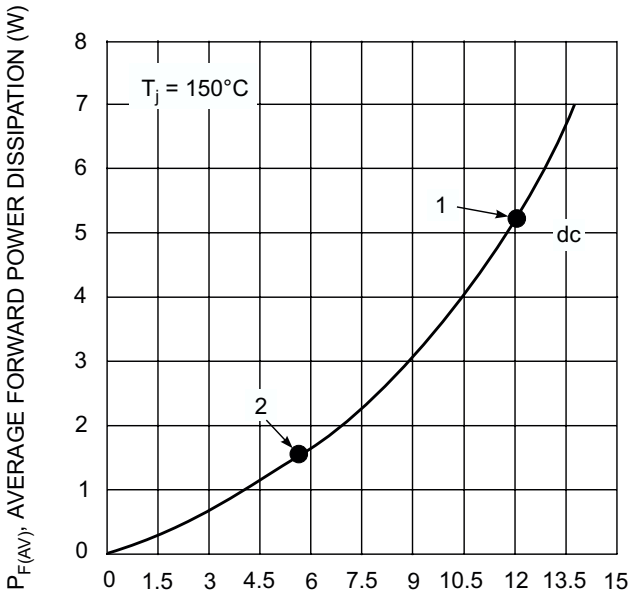


Fig. 5 Forward Power Dissipation

Notes: 1. Device mounted on GETEK substrate, 2"x2", 2 oz. copper, double-sided, cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0". $R_{\theta JA}$ in range of 15-30°C/W.

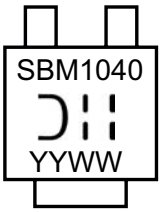
2. Device mounted on FR-4 substrate, 2"x2", 2 oz. copper, single-sided, pad layout as per Diodes Inc. suggested pad layout document AP02001 which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf. $R_{\theta JA}$ in range of 60-75°C/W.

Ordering Information (Note 3)

Device	Packaging	Shipping
SBM1040-13	POWERMITE®3	5000/Tape & Reel

Notes: 3. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



SBM1040 = Product type marking code
= Manufacturers' code marking
YYWW = Date code marking
YY = Last two digits of year ex: 02 for 2002
WW = Week code 01 to 52

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